

VHF/UHF Transistor

NPN Silicon

MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

Features

- S and NSV Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V_{CEO}	Collector-Emitter Voltage	25	Vdc
V_{CBO}	Collector-Base Voltage	30	Vdc
V_{EBO}	Emitter-Base Voltage	3.0	Vdc

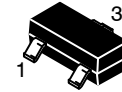
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

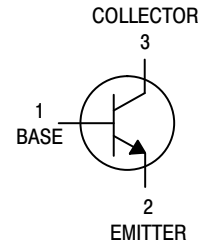
Symbol	Characteristic	Max	Unit
P_D	Total Device Dissipation FR-5 Board (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	225 1.8	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 2)	556	$^\circ\text{C}/\text{W}$
P_D	Total Device Dissipation Alumina Substrate (Note 3) $T_A = 25^\circ\text{C}$ Derate above 25°C	300 2.4	mW mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 3)	417	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

2. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

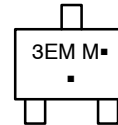
3. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina



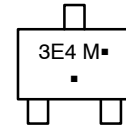
SOT-23 (TO-236)
CASE 318
STYLE 6



MARKING DIAGRAMS



MMBTH10LT1G,
NSVMMBTH10LT1G



MMBTH10-04LT1G

3EM, 3E4 = Specific Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

* Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBTH10LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVMMBTH10LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTH10LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

DISCONTINUED (Note 1)

MMBTH10-4LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTH10-4LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

1. **DISCONTINUED:** These devices are not available. Please contact your onsemi representative for information. The most current information on these devices may be available on [www.onsemi.com](#).

MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C = 1.0\text{ mA}$, $I_E = 0$)	25	–	–	Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{A}$, $I_E = 0$)	30	–	–	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{A}$, $I_C = 0$)	3.0	–	–	Vdc
I_{CBO}	Collector Cutoff Current ($V_{CB} = 25\text{ Vdc}$, $I_E = 0$)	–	–	100	nAdc
I_{EBO}	Emitter Cutoff Current ($V_{EB} = 2.0\text{ Vdc}$, $I_C = 0$)	–	–	100	nAdc

ON CHARACTERISTICS

h_{FE}	DC Current Gain ($I_C = 4.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$) MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10-4LT1G, SMMBTH10-4LT3G	60 120	– –	– 240	–
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C = 4.0\text{ mA}$, $I_E = 0.4\text{ mA}$)	–	–	0.5	Vdc
V_{BE}	Base-Emitter On Voltage ($I_C = 4.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$)	–	–	0.95	Vdc

SMALL-SIGNAL CHARACTERISTICS

f_T	Current-Gain - Bandwidth Product ($I_C = 4.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$) MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10-4LT1G, SMMBTH10-4LT3G	650 800	– –	– –	MHz
C_{cb}	Collector-Base Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	–	–	0.7	pF
C_{rb}	Common-Base Feedback Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	–	–	0.65	pF
$r_b'C_c$	Collector Base Time Constant ($I_C = 4.0\text{ mA}$, $V_{CB} = 10\text{ Vdc}$, $f = 31.8\text{ MHz}$)	–	–	9.0	ps

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



TYPICAL CHARACTERISTICS

COMMON-BASE y PARAMETERS versus FREQUENCY

($V_{CB} = 10 \text{ Vdc}$, $I_C = 4.0 \text{ mA dc}$, $T_A = 25^\circ \text{C}$)

y_{ib} , INPUT ADMITTANCE

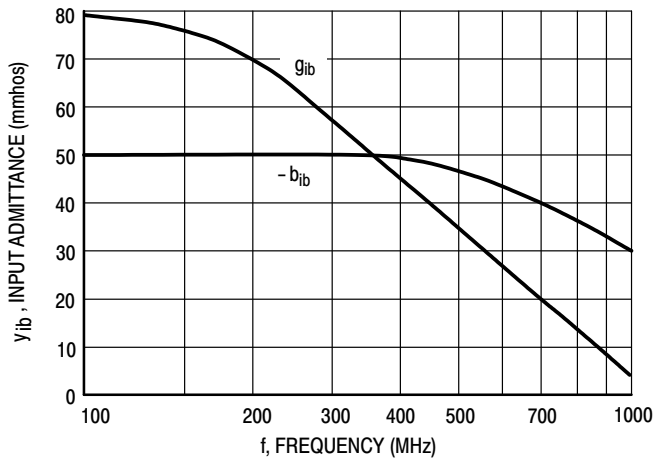


Figure 1. Rectangular Form

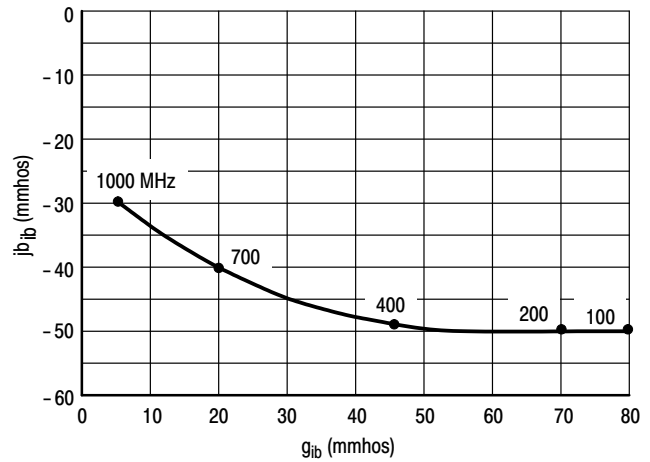


Figure 2. Polar Form

y_{fb} , FORWARD TRANSFER ADMITTANCE

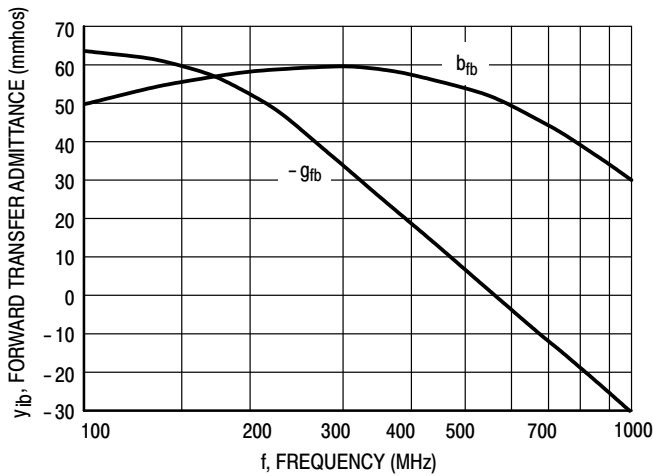


Figure 3. Rectangular Form

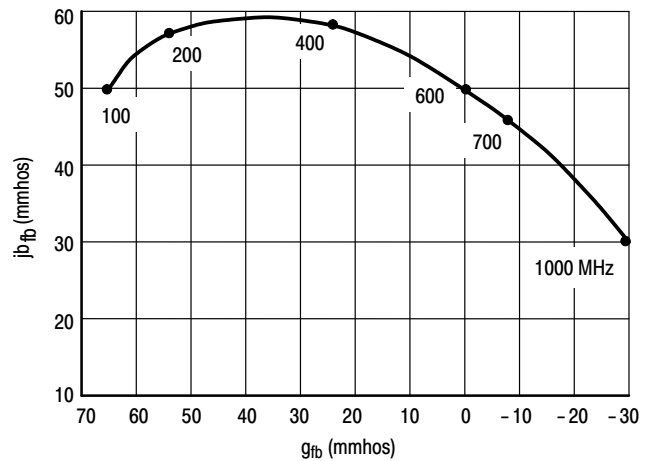


Figure 4. Polar Form

TYPICAL CHARACTERISTICS

COMMON-BASE y PARAMETERS versus FREQUENCY

($V_{CB} = 10 \text{ Vdc}$, $I_C = 4.0 \text{ mAdc}$, $T_A = 25^\circ\text{C}$)

y_{rb} , REVERSE TRANSFER ADMITTANCE

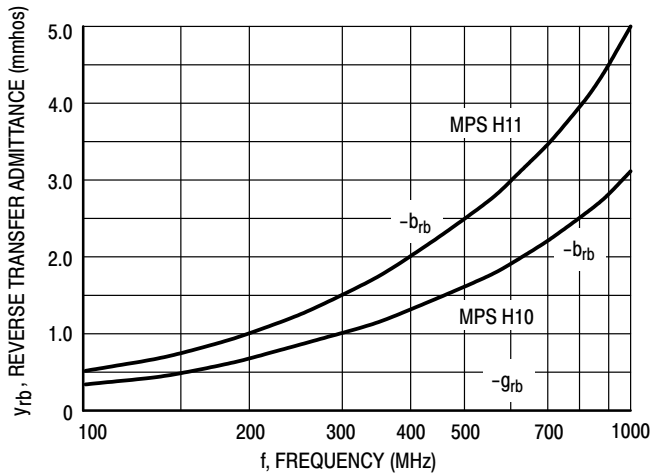


Figure 5. Rectangular Form

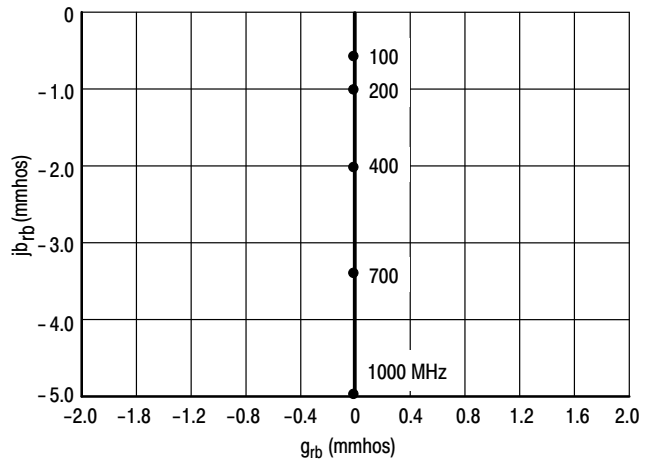


Figure 6. Polar Form

y_{ob} , OUTPUT ADMITTANCE

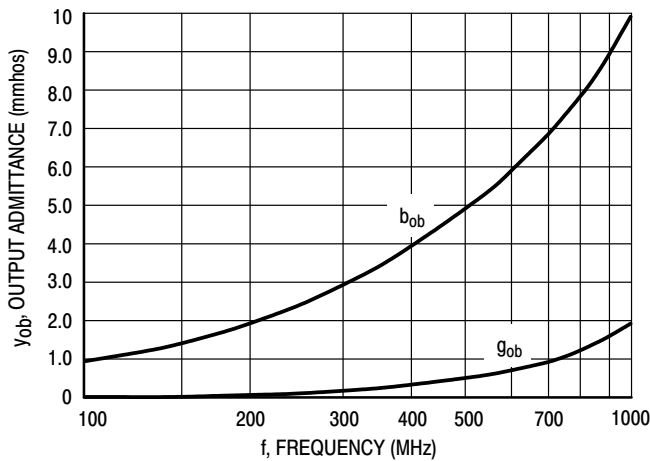


Figure 7. Rectangular Form

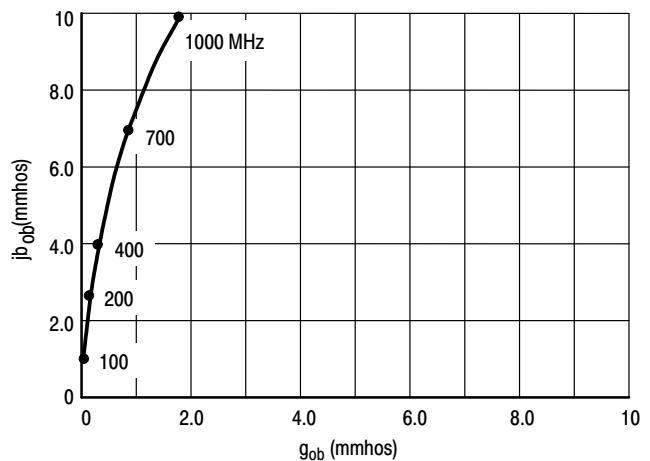


Figure 8. Polar Form

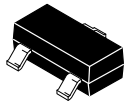
MMBTH10L, MMBTH10-4L, SMMBTH10-4L, NSVMMBTH10L

REVISION HISTORY

Revision	Description of Changes	Date
8	MMBTH10-4LT1G, SMMBTH10-4LT3G OPN's Marked as Discontinued.	01/16/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

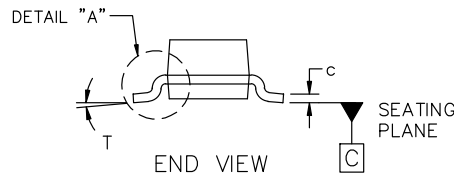
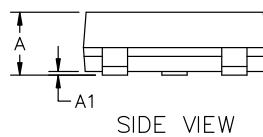
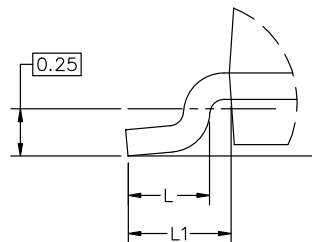
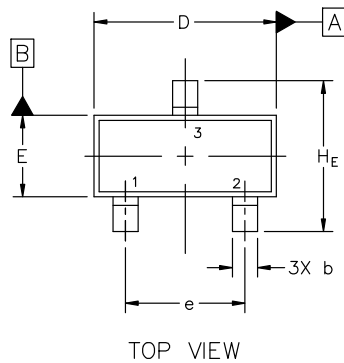




SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

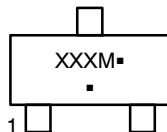


MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

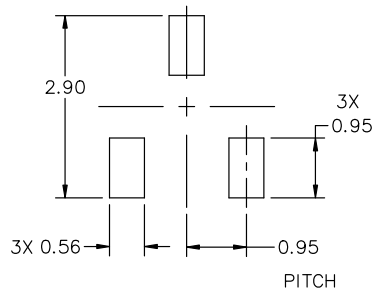
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

STYLES ON PAGE 2

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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